

ABSTRACT OF THE DISCLOSURE

A manufacturing method of a thin film transistor of a liquid crystal display device using 3-mask includes forming a gate electrode over a substrate, consecutively forming a gate insulating layer and an active layer, forming a first photoresist pattern, removing an active layer formed at a source/drain region, ashing the first photoresist pattern to expose a part of an active region, forming a source/drain electrode, forming a passivation layer, forming a second photoresist pattern that exposes a pixel region over the passivation layer; forming a pixel region by using the second photoresist pattern as a mask, side-etching a part of the passivation layer to expose a part of the drain electrode, forming a pixel electrode material over the second photoresist pattern and the pixel region, and simultaneously removing the second photoresist pattern and the pixel electrode material formed thereon to form a pixel electrode.